

Features

- **Fast Read Access Time - 70 ns**
- **Automatic Page Write Operation**
Internal Address and Data Latches for 64 Bytes
Internal Control Timer
- **Fast Write Cycle Times**
Page Write Cycle Time: 10 ms or 3 ms maximum
1 to 64 Byte Page Write Operation
- **Low Power Dissipation**
80 mA Active Current
3 mA Standby Current (AT28HC256L)
- **Hardware and Software Data Protection**
- **DATA Polling for End of Write Detection**
- **High Reliability CMOS Technology**
Endurance: 10⁴ or 10⁵ Cycles
Data Retention: 10 years
- **Single 5 V ± 10% Supply**
- **CMOS and TTL Compatible Inputs and Outputs**
- **JEDEC Approved Byte-Wide Pinout**
- **Full Military, Commercial, and Industrial Temperature Ranges**

**256 (32K x 8)
High Speed
CMOS
E²PROM**

Description

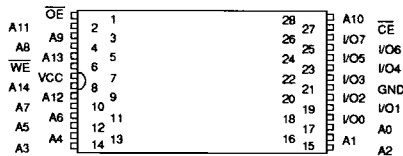
The AT28HC256/L is a high-performance Electrically Erasable and Programmable Read Only Memory. Its 256K of memory is organized as 32,768 words by 8 bits. Manufactured with Atmel's advanced nonvolatile CMOS technology, the AT28HC256 offers access times to 70 ns with power dissipation of just 440 mW. When the AT28HC256L is deselected, the standby current is less than 5 mA.

The AT28HC256/L is accessed like a Static RAM for the read or write cycle without the need for external components. The device contains a 64-byte page register to allow writing of up to

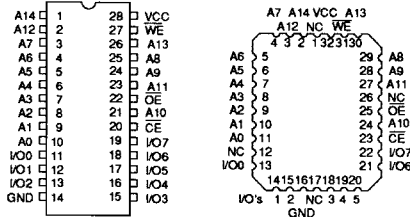
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Pin Configurations

TSOP Top View



Pin Name	Function
A0 - A14	Addresses
CE	Chip Enable
OE	Output Enable
WE	Write Enable
I/O0 - I/O7	Data Inputs/Outputs
NC	No Connect



Note: PLCC package pins 1 and 17 are DON'T CONNECT.



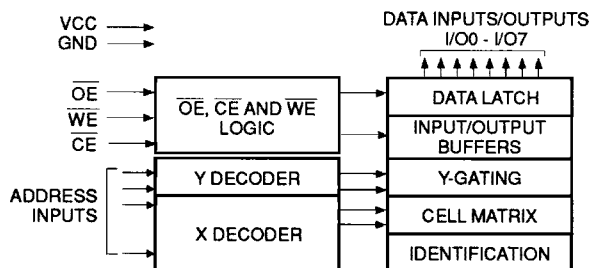


Description (Continued)

64 bytes simultaneously. During a write cycle, the address and 1 to 64 bytes of data are internally latched, freeing the addresses and data bus for other operations. Following the initiation of a write cycle, the device will automatically write the latched data using an internal control timer. The end of a write cycle can be detected by $\overline{\text{DATA}}$ polling of I/O7. Once the end of a write cycle has been detected a new access for a read or write can begin.

Atmel's 28HC256/L has additional features to ensure high quality and manufacturability. The device utilizes internal error correction for extended endurance and improved data retention characteristics. An optional software data protection mechanism is available to guard against inadvertent writes. The device also includes an extra 64 bytes of E²PROM for device identification or tracking.

Block Diagram



Absolute Maximum Ratings*

Temperature Under Bias.....	-55°C to +125°C
Storage Temperature.....	-65°C to +150°C
All Input Voltages (including N.C. Pins) with Respect to Ground	-0.6 V to +6.25 V
All Output Voltages with Respect to Ground	-0.6 V to V _{CC} +0.6 V
Voltage on $\overline{\text{OE}}$ and A9 with Respect to Ground	-0.6 V to +13.5 V

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Device Operation

READ: The AT28C256 is accessed like a Static RAM. When \overline{CE} and \overline{OE} are low and \overline{WE} is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in the high impedance state when either \overline{CE} or \overline{OE} is high. This dual-line control gives designers flexibility in preventing bus contention in their system.

BYTE WRITE: A low pulse on the \overline{WE} or \overline{CE} input with \overline{CE} or \overline{WE} low (respectively) and \overline{OE} high initiates a write cycle. The address is latched on the falling edge of \overline{CE} or \overline{WE} , whichever occurs last. The data is latched by the first rising edge of \overline{CE} or \overline{WE} . Once a byte write has been started it will automatically time itself to completion.

PAGE WRITE: The page write operation of the AT28C256 allows one to sixty-four bytes of data to be written into the device during a single internal programming period. A page write operation is initiated in the same manner as a byte write; the first byte written can then be followed by one to sixty-three additional bytes. Each successive byte must be written within 150 μ s (t_{BLC}) of the previous byte. If the t_{BLC} limit is exceeded the AT28C256 will cease accepting data and commence the internal programming operation. All bytes during a page write operation must reside on the same page as defined by the state of the A6-A14 inputs. That is, for each \overline{WE} high to low transition during the page write operation, A6 - A14 must be the same.

The A0 to A5 inputs are used to specify which bytes within the page are to be written. The bytes may be loaded in any order and may be altered within the same load period. Only bytes which are specified for writing will be written; unnecessary cycling of other bytes within the page does not occur.

DATA POLLING: The AT28C256 features \overline{DATA} Polling to indicate the end of a write cycle. During a byte or page write cycle an attempted read of the last byte written will result in the complement of the written data to be presented on I/O7. Once the write cycle has been completed, true data is valid on all outputs, and the next write cycle may begin. \overline{DATA} Polling may begin at anytime during the write cycle.

TOGGLE BIT: In addition to \overline{DATA} Polling the AT28C256 provides another method for determining the end of a write cycle. During the write operation, successive attempts to read data from the device will result in I/O6 toggling between one and zero. Once the write has completed, I/O6 will stop toggling and valid data will be read. Testing the toggle bit may begin at any time during the write cycle.

DATA PROTECTION: If precautions are not taken, inadvertent writes to any five-volt-only nonvolatile memory may occur dur-

ing transition of the host system power supply. Atmel has incorporated both hardware and software features that will protect the memory against inadvertent writes.

HARDWARE PROTECTION: Hardware features protect against inadvertent writes to the AT28C256 in the following ways: (a) V_{CC} sense - if V_{CC} is below 3.8 V (typical) the write function is inhibited; (b) V_{CC} power-on delay - once V_{CC} has reached 3.8 V the device will automatically time out 5 ms (typical) before allowing a write; (c) write inhibit - holding any one of \overline{OE} low, \overline{CE} high or \overline{WE} high inhibits write cycles; (d) noise filter - pulses of less than 15 ns (typical) on the \overline{WE} or \overline{CE} inputs will not initiate a write cycle.

SOFTWARE DATA PROTECTION: A software controlled data protection feature has been implemented on the AT28C256. When enabled, the software data protection (SDP), will prevent inadvertent writes. The SDP feature may be enabled or disabled by the user; the AT28C256 is shipped from Atmel with SDP disabled.

SDP is enabled by the host system issuing a series of three write commands; three specific bytes of data are written to three specific addresses (refer to Software Data Protection Algorithm). After writing the three byte command sequence and after twc the entire AT28C256 will be protected against inadvertent write operations. It should be noted, that once protected the host may still perform a byte or page write to the AT28C64B. This is done by preceding the data to be written by the same three byte command sequence.

Once set, SDP will remain active unless the disable command sequence is issued. Power transitions do not disable SDP and SDP will protect the AT28C256 during power-up and power-down conditions. All command sequences must conform to the page write timing specifications. It should also be noted that the data in the enable and disable command sequences is not written to the device and the memory addresses used in the sequence may be written with data in either a byte or page write operation.

After setting SDP, any attempt to write to the device without the three byte command sequence will start the internal write timers. No data will be written to the device; however, for the duration of twc, read operations will effectively be polling operations.

DEVICE IDENTIFICATION: An extra 64 bytes of E²PROM memory are available to the user for device identification. By raising A9 to 12 V \pm 0.5 V and using address locations 7FC0H to 7FFFH the additional bytes may be written to or read from in the same manner as the regular memory array.

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Pin Capacitance (f = 1 MHz, T = 25°C) ⁽¹⁾

	Typ	Max	Units	Conditions
C _{IN}	4	6	pF	V _{IN} = 0 V
C _{OUT}	8	12	pF	V _{OUT} = 0 V

Note: 1. This parameter is characterized and is not 100% tested.





D.C. and A.C. Operating Range

		AT28HC256-70	AT28HC256L-90	AT28HC256-90	AT28HC256/L-12
Operating Temperature (Case)	Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C	0°C - 70°C
	Ind.	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C
	Mil.			-55°C - 125°C	-55°C - 125°C
V _{CC} Power Supply		5 V ± 10%	5 V ± 10%	5 V ± 10%	5 V ± 10%

Operating Modes

Mode	\overline{CE}	\overline{OE}	\overline{WE}	I/O
Read	V _{IL}	V _{IL}	V _{IH}	D _{OUT}
Write ⁽²⁾	V _{IL}	V _{IH}	V _{IL}	D _{IN}
Standby/Write Inhibit	V _{IH}	X ⁽¹⁾	X	High Z
Write Inhibit	X	X	V _{IH}	
Write Inhibit	X	V _{IL}	X	
Output Disable	X	V _{IH}	X	High Z
Chip Erase	V _{IL}	V _H ⁽³⁾	V _{IL}	High Z

Notes: 1. X can be V_{IL} or V_{IH}.

2. Refer to A.C. Programming Waveforms.

3. V_H = 12.0 V ± 0.5 V.

D.C. Characteristics

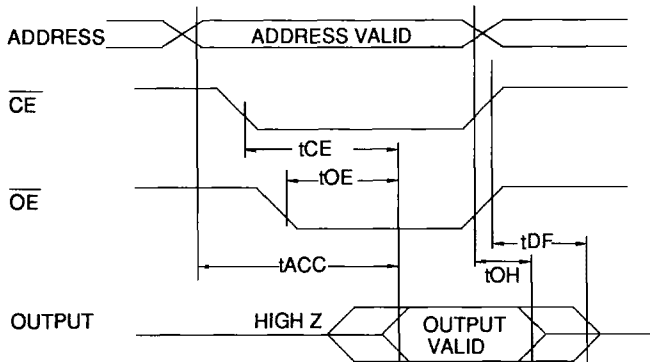
Symbol	Parameter	Condition	Min	Max	Units
I _{LI}	Input Load Current	V _{IN} = 0 V to V _{CC} + 1 V		10	μA
I _{LO}	Output Leakage Current	V _{I/O} = 0V to V _{CC}		10	μA
I _{SB1}	V _{CC} Standby Current TTL	$\overline{CE} = 2.0$ V to V _{CC} + 1 V	AT28HC256L	3	mA
			AT28HC256	60	mA
I _{SB2}	V _{CC} Standby Current CMOS	$\overline{CE} = -3.0$ V to V _{CC} + 1 V	AT28HC256L	300	μA
I _{CC}	V _{CC} Active Current	f = 5 MHz; I _{OUT} = 0 mA		80	mA
V _{IL}	Input Low Voltage			0.8	V
V _{IH}	Input High Voltage		2.0		V
V _{OL}	Output Low Voltage	I _{OL} = 6.0 mA		.45	V
V _{OH}	Output High Voltage	I _{OH} = -4 mA	2.4		V

A.C. Read Characteristics

Symbol	Parameter	AT28HC256-70		AT28C256/L-90		AT28HC256/L-12		Units
		Min	Max	Min	Max	Min	Max	
t_{ACC}	Address to Output Delay		70		90		120	ns
$t_{CE}^{(1)}$	\overline{CE} to Output Delay		70		90		120	ns
$t_{OE}^{(2)}$	\overline{OE} to Output Delay	0	35	0	40	0	50	ns
$t_{DF}^{(3,4)}$	\overline{CE} or \overline{OE} to Output Float	0	35	0	40	0	50	ns
t_{OH}	Output Hold from \overline{OE} , \overline{CE} or Address, whichever occurred first	0		0		0		ns

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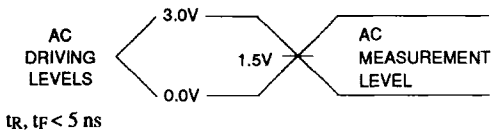
A.C. Read Waveforms



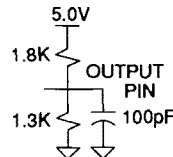
Notes:

- \overline{CE} may be delayed up to $t_{ACC} - t_{CE}$ after the address transition without impact on t_{ACC} .
- \overline{OE} may be delayed up to $t_{CE} - t_{OE}$ after the falling edge of \overline{CE} without impact on t_{CE} or by $t_{ACC} - t_{OE}$ after an address change without impact on t_{ACC} .
- t_{DF} is specified from \overline{OE} or \overline{CE} whichever occurs first ($C_L = 5 \text{ pF}$).
- This parameter is characterized and is not 100% tested.

Input Test Waveforms and Measurement Level



Output Test Load

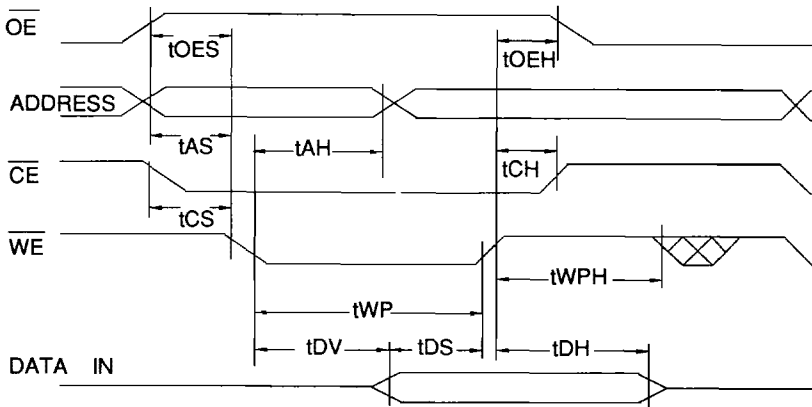


A.C. Write Characteristics

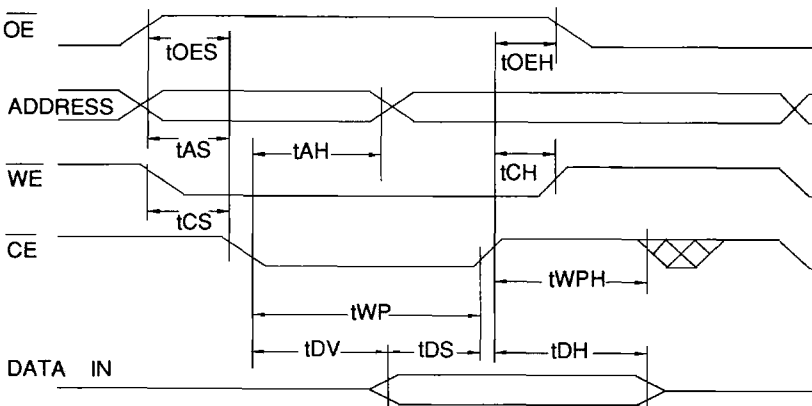
Symbol	Parameter	Min	Max	Units
tAS, tOES	Address, \overline{OE} Set-up Time	0		ns
tAH	Address Hold Time	50		ns
tCS	Chip Select Set-up Time	0		ns
tCH	Chip Select Hold Time	0		ns
tWP	Write Pulse Width (\overline{WE} or \overline{CE})	100		ns
tDS	Data Set-up Time	50		ns
tDH, tOEH	Data, \overline{OE} Hold Time	0		ns
tDV	Time to Data Valid	NR ⁽¹⁾		
twc	Write Cycle Time	AT28HC256	10	ms
		AT28HC256F	3.0	ms

Note: 1. NR = No Restriction

A.C. Write Waveforms- \overline{WE} Controlled



A.C. Write Load Waveforms- \overline{CE} Controlled

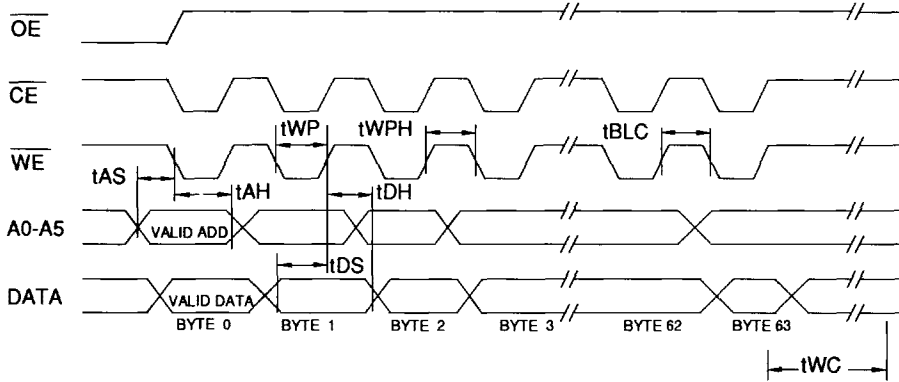


Page Mode Write Characteristics

Symbol	Parameter	Min	Typ	Max	Units
t _{WC}	Write Cycle Time	AT28HC256	5	10	ms
		AT28HC256F	2	3.0	ms
t _{AS}	Address Set-up Time	0			ns
t _{AH}	Address Hold Time	50			ns
t _{DS}	Data Set-up Time	50			ns
t _{DH}	Data Hold Time	0			ns
t _{WP}	Write Pulse Width	100			ns
t _{BLC}	Byte Load Cycle Time			150	μs
t _{WPH}	Write Pulse Width High	50			ns

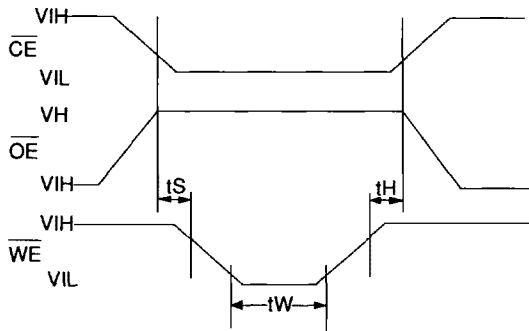
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Page Mode Write Waveforms



Notes: A6 through A14 must specify the same page address during each high to low transition of \overline{WE} (or \overline{CE}).
 \overline{OE} must be high only when \overline{WE} and \overline{CE} are both low.

Chip Erase Waveforms

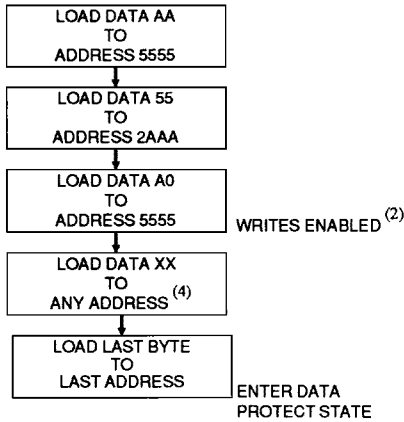


$t_S = t_H = 5 \mu\text{sec (min.)}$
 $t_W = 10 \text{ msec (min.)}$
 $V_{IH} = 12.0 \text{ V} \pm 0.5 \text{ V}$

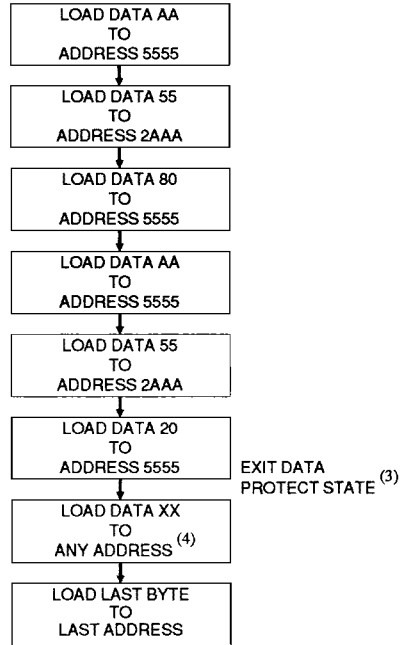




Software Data Protection Enable Algorithm ⁽¹⁾



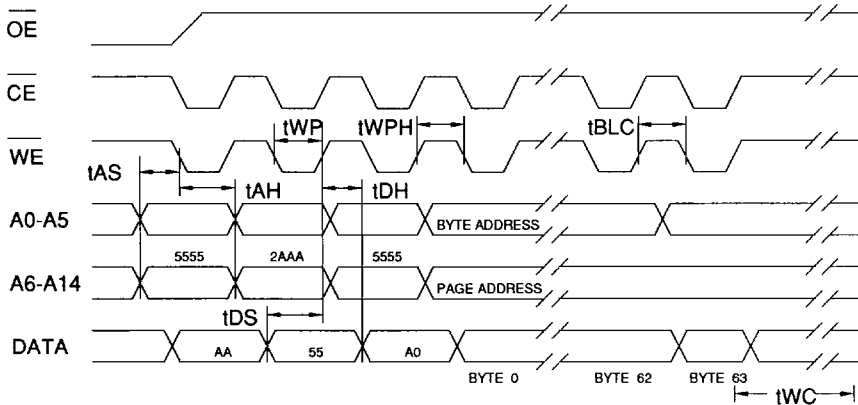
Software Data Protection Disable Algorithm ⁽¹⁾



Notes:

1. Data Format: I/O7 - I/O0 (Hex);
Address Format: A14 - A0 (Hex).
2. Write Protect state will be activated at end of write even if no other data is loaded.
3. Write Protect state will be deactivated at end of write period even if no other data is loaded.
4. 1 to 64 bytes of data are loaded.

Software Protected Write Cycle Waveforms



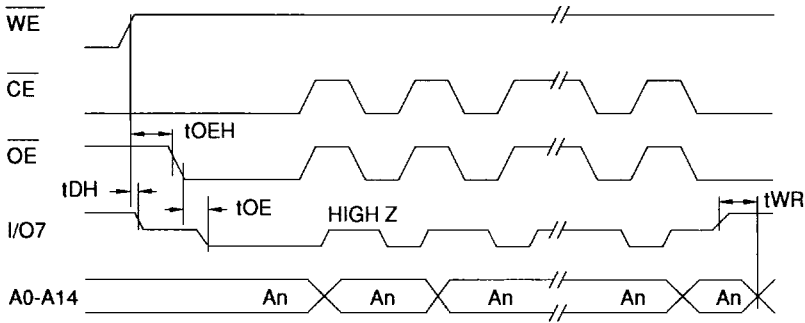
- Notes:
- A6 through A14 must specify the same page address during each high to low transition of \overline{WE} (or \overline{CE}) after the software code has been entered.
 - \overline{OE} must be high only when \overline{WE} and \overline{CE} are both low.

Data Polling Characteristics⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Units
t _{DH}	Data Hold Time	0			ns
t _{OEH}	\overline{OE} Hold Time	0			ns
t _{OE}	\overline{OE} to Output Delay			100	ns
t _{WR}	Write Recovery Time	0			ns

Note: 1. These parameters are characterized and not 100% tested.

Data Polling Waveforms

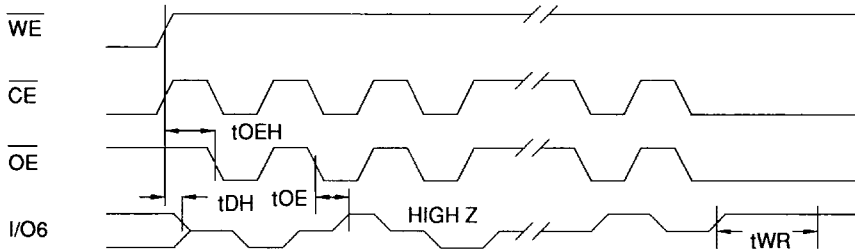


Toggle Bit Characteristics⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Units
t _{DH}	Data Hold Time	10			ns
t _{OEH}	\overline{OE} Hold Time	10			ns
t _{OE}	\overline{OE} to Output Delay			100	ns
t _{OEHP}	\overline{OE} High Pulse	150			ns
t _{WR}	Write Recovery Time	0			ns

Note: 1. These parameters are characterized and not 100% tested.

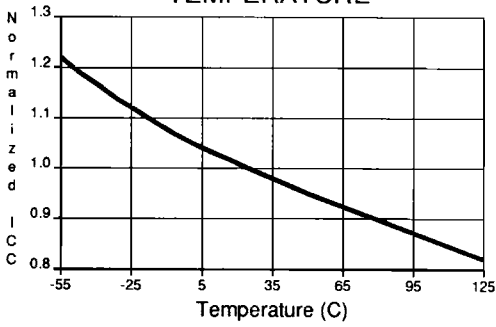
Toggle Bit Waveforms



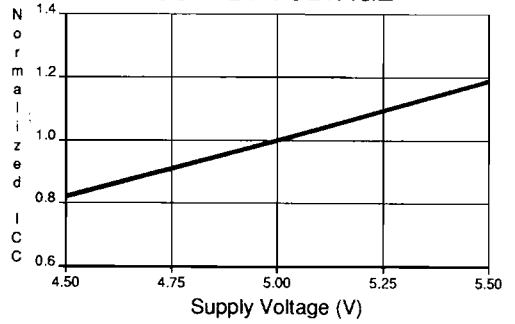
Notes:

1. Toggling either \overline{OE} or \overline{CE} or both \overline{OE} and \overline{CE} will operate toggle bit.
2. Beginning and ending state of I/O6 will vary.
3. Any address location may be used but the address should not vary.

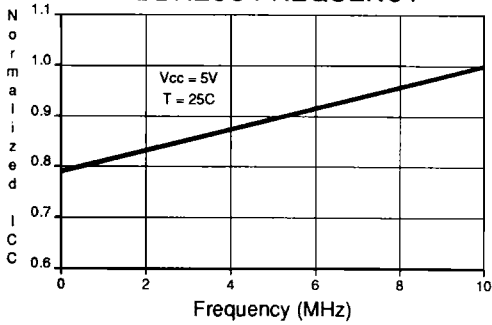
NORMALIZED SUPPLY CURRENT vs. TEMPERATURE



NORMALIZED SUPPLY CURRENT vs. SUPPLY VOLTAGE



NORMALIZED SUPPLY CURRENT vs. ADDRESS FREQUENCY



Ordering Information

t _{acc} (ns)	I _{cc} (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
70	80	60	AT28HC256(E,F)-70DC AT28HC256(E,F)-70JC AT28HC256(E,F)-70PC	28D6 32J 28P6	Commercial (0°C to 70°C)
			AT28HC256(E,F)-70DI AT28HC256(E,F)-70JI AT28HC256(E,F)-70PI	28D6 32J 28P6	Industrial (-40°C to 85°C)
90	80	60	AT28HC256(E,F)-90DC AT28HC256(E,F)-90JC AT28HC256(E,F)-90PC AT28HC256(E,F)-90UC	28D6 32J 28P6 28U	Commercial (0°C to 70°C)
			AT28HC256(E,F)-90DI AT28HC256(E,F)-90JI AT28HC256(E,F)-90PI AT28HC256(E,F)-90UI	28D6 32J 28P6 28U	Industrial (-40°C to 85°C)
			AT28HC256(E,F)-90DM/883 AT28HC256(E,F)-90FM/883 AT28HC256(E,F)-90LM/883 AT28HC256(E,F)-90UM/883	28D6 28F 32L 28U	Military/883C Class B, Fully Compliant (-55°C to 125°C)
120	80	60	AT28HC256(E,F)-12DC AT28HC256(E,F)-12JC AT28HC256(E,F)-12PC AT28HC256(E,F)-12TC AT28HC256(E,F)-12UC	28D6 32J 28P6 28T 28U	Commercial (0°C to 70°C)
			AT28HC256(E,F)-12DI AT28HC256(E,F)-12JI AT28HC256(E,F)-12PI AT28HC256(E,F)-12TI AT28HC256(E,F)-12UI	28D6 32J 28P6 28T 28U	Industrial (-40°C to 85°C)
			AT28HC256(E,F)-12DM/883 AT28HC256(E,F)-12FM/883 AT28HC256(E,F)-12LM/883 AT28HC256(E,F)-12UM/883	28D6 28F 32L 28U	Military/883C Class B, Fully Compliant (-55°C to 125°C)
90	80	60	5962-88634 03 UX 5962-88634 03 XX 5962-88634 03 YX 5962-88634 03 ZX	28U 28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)
			5962-88634 04 UX 5962-88634 04 XX 5962-88634 04 YX 5962-88634 04 ZX	28U 28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)

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Ordering Information

Package Type	
28D6	28 Lead, 0.600" Wide, Non-Windowed, Ceramic Dual Inline Package (Cerdip)
28F	28 Lead, Non-Windowed, Ceramic Bottom-Brazed Flat Package (Flatpack)
32J	32 Lead, Plastic J-Leaded Chip Carrier (PLCC)
32L	32 Pad, Non-Windowed, Ceramic Leadless Chip Carrier (LCC)
28P6	28 Lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)
28T	28 Lead, Plastic Thin Small Outline Package (TSOP)
28U	28 Pin, Ceramic Pin Grid Array (PGA)
Options	
Blank	Standard Device: Endurance = 10K Write Cycles; Write Time = 10 ms
E	High Endurance Option: Endurance = 100K Write Cycles
F	Fast Write Option: Write Time = 3 ms

Ordering Information

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t _{ACC} (ns)	I _{CC} (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
90	80	0.3	AT28HC256L(E,F)-90DC AT28HC256L(E,F)-90JC AT28HC256L(E,F)-90PC AT28HC256L(E,F)-90UC	28D6 32J 28P6 28U	Commercial (0°C to 70°C)
			AT28HC256L(E,F)-90DI AT28HC256L(E,F)-90JI AT28HC256L(E,F)-90PI AT28HC256L(E,F)-90UI	28D6 32J 28P6 28U	Industrial (-40°C to 85°C)
120	80	0.3	AT28HC256L(E,F)-12DC AT28HC256L(E,F)-12JC AT28HC256L(E,F)-12PC AT28HC256L(E,F)-12UC AT28HC256L-W	28D6 32J 28P6 28U DIE	Commercial (0°C to 70°C)
			AT28HC256L(E,F)-12DI AT28HC256L(E,F)-12JI AT28HC256L(E,F)-12PI AT28HC256L(E,F)-12UI	28D6 32J 28P6 28U	Industrial (-40°C to 85°C)
			AT28HC256L(E,F)-12DM/883 AT28HC256L(E,F)-12FM/883 AT28HC256L(E,F)-12LM/883 AT28HC256L(E,F)-12UM/883	28D6 28F 32L 28U	Military/883C Class B, Fully Compliant (-55°C to 125°C)
120	80	0.3	5962-88634 01 UX 5962-88634 01 XX 5962-88634 01 YX 5962-88634 01 ZX	28U 28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)
			5962-88634 02 UX 5962-88634 02 XX 5962-88634 02 YX 5962-88634 02 ZX	28U 28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)

Package Type	
28D6	28 Lead, 0.600" Wide, Non-Windowed, Ceramic Dual Inline Package (Cerdip)
28F	28 Lead, Non-Windowed, Ceramic Bottom-Brazed Flat Package (Flatpack)
32J	32 Lead, Plastic J-Leaded Chip Carrier (PLCC)
32L	32 Pad, Non-Windowed, Ceramic Leadless Chip Carrier (LCC)
28P6	28 Lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)
28U	28 Pin, Ceramic Pin Grid Array (PGA)
W	Die
Options	
Blank	Standard Device: Endurance = 10K Write Cycles; Write Time = 10 ms
E	High Endurance Option: Endurance = 100K Write Cycles
F	Fast Write Option: Write Time = 3 ms



